



### 30V P-Channel Enhancement Mode MOSFET

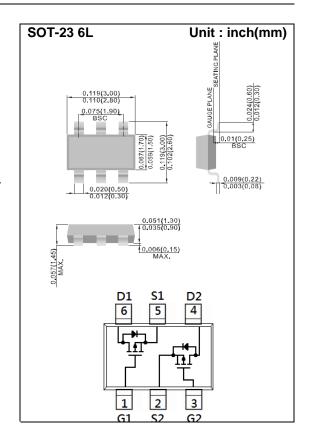
Voltage -30 V Current -2.6A

#### **Features**

- RDS(ON), VGS@-10V, ID@-2.6A<115m $\Omega$
- RDS(ON) , VGS@-4.5V, ID@-1.7A<150mΩ</li>
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams
- Marking: ST9



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-30	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	-2.6	Α
Pulsed Drain Current		I <sub>DM</sub>	-10.4	Α
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.25	W
	Derate above 25°C		10	mW/°C
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C
Typical Thermal resistance - Junction to Ambient (Note 3)		$R_{ heta JA}$	100	°C/W





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-1	-1.31	-2.1	V		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.6A	-	93	115	mΩ		
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.7A	-	116	150			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-0.01	-1	uA		
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA		
Dynamic								
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-15V, I <sub>D</sub> =-2.6A, V <sub>GS</sub> =-10V <sup>(Note 1,2)</sup>	-	9.8	-	nC		
Gate-Source Charge	$Q_gs$		-	1.5	-			
Gate-Drain Charge	$Q_{gd}$		-	2.2	-			
Input Capacitance	Ciss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	396	-	pF		
Output Capacitance	Coss		-	47	-			
Reverse Transfer Capacitance	Crss		-	36	-			
Switching								
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =-15V, $I_{D}$ =-2.6A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	5	-			
Turn-On Rise Time	tr		-	30	-	ns		
Turn-Off Delay Time	td <sub>(off)</sub>		-	25	-			
Turn-Off Fall Time	tf		-	8	-			
Drain-Source Diode								
Maximum Continuous Drain-Source			-	-	-1.5	А		
Diode Forward Current	I <sub>S</sub>							
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-0.77	-1.2	V		

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited





#### **TYPICAL CHARACTERISTIC CURVES**

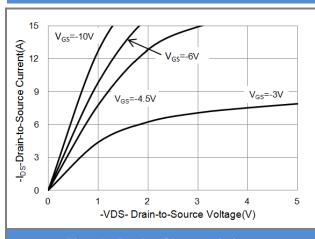
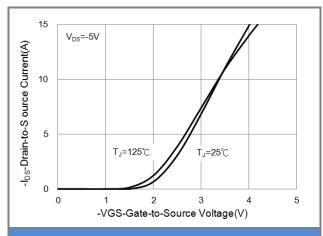


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

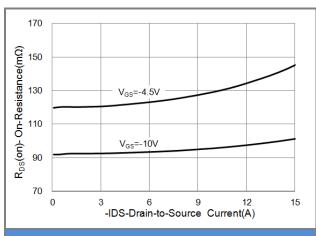


Fig.3 On-Resistance vs. Drain Current

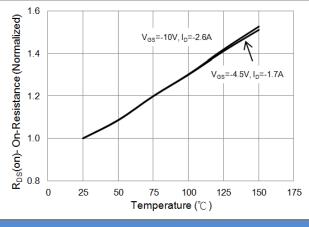


Fig.4 On-Resistance vs. Junction temperature

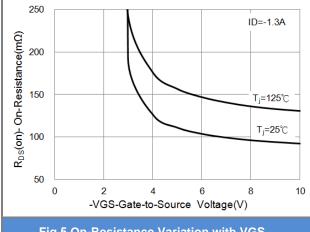


Fig.5 On-Resistance Variation with VGS.

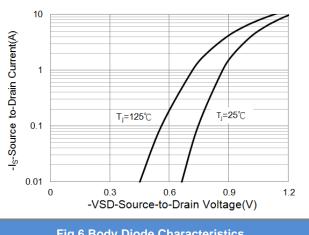


Fig.6 Body Diode Characteristics





### **TYPICAL CHARACTERISTIC CURVES**

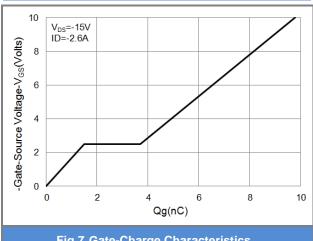


Fig.7 Gate-Charge Characteristics

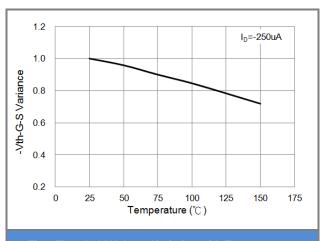


Fig.8 Threshold Voltage Variation with Temperature

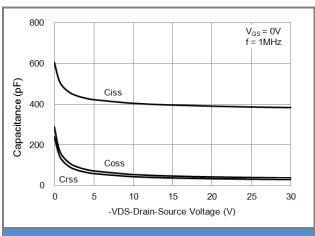


Fig.9 Capacitance vs. Drain-Source Voltage

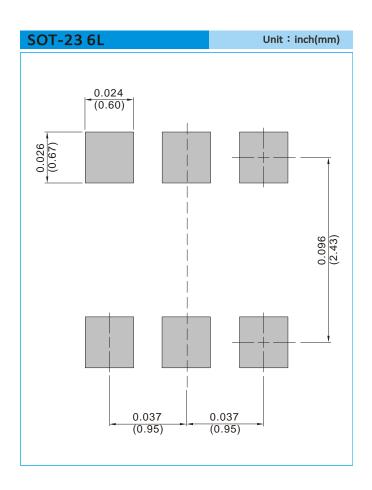




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6809_S1_00001	SOT-23 6L	3K pcs / 7" reel	ST9	Halogen free
PJS6809_S2_00001	SOT-23 6L	10K pcs / 13" reel	ST9	Halogen free

### **MOUNTING PAD LAYOUT**







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